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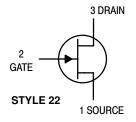
JFET VHF/UHF Amplifiers

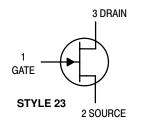
N–Channel — Depletion

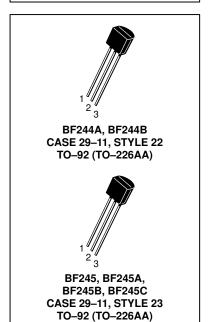
BF245A BF245B

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	±30	Vdc
Drain-Gate Voltage	V _{DG}	30	Vdc
Gate-Source Voltage	V _{GS}	30	Vdc
Drain Current	ΙD	100	mAdc
Forward Gate Current	I _{G(f)}	10	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	350 2.8	mW mW/°C
Storage Channel Temperature Range	T _{stg}	-65 to +150	°C







ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteris	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS		•	1			
Gate-Source Breakdown Voltage $(I_G = 1.0 \mu Adc, V_{DS} = 0)$		V _(BR) GSS	30	_	_	Vdc
Gate-Source (V _{DS} = 15 Vdc, I _D = 200 μAdc)	BF245 ⁽¹⁾ BF245A, BF244A ⁽²⁾ BF245B, BF244B BF245C	V _G S	0.4 0.4 1.6 3.2	_ _ _ _	7.5 2.2 3.8 7.5	Vdc
Gate-Source Cutoff Voltage (V _{DS} = 15 Vdc, I _D = 10 nAdc)		V _{GS(off)}	-0.5	_	-8.0	Vdc
Gate Reverse Current (V _{GS} = 20 Vdc, V _{DS} = 0)		lgss	_	_	5.0	nAdc
ON CHARACTERISTICS		•				
Zero-Gate-Voltage Drain Current (V _{DS} = 15 Vdc, V _{GS} = 0)	BF245(1) BF245A, BF244A(2) BF245B, BF244B BF245C	IDSS	2.0 2.0 6.0 12	_ _ _ _	25 6.5 15 25	mAdc

- 1. On orders against the BF245, any or all subgroups might be shipped.
- 2. On orders against the BF244A, any or all subgroups might be shipped.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

Characteristic			Min	Тур	Max	Unit
SMALL-SIGNAL CHARACTERISTICS						
Forward Transfer Admittance	$(V_{DS} = 15 \text{ Vdc}, V_{GS} = 0, f = 1.0 \text{ kHz})$	Yfs	3.0	_	6.5	mmhos
Output Admittance	$(V_{DS} = 15 \text{ Vdc}, V_{GS} = 0, f = 1.0 \text{ kHz})$	Yos	_	40	_	μmhos
Forward Transfer Admittance	$(V_{DS} = 15 \text{ Vdc}, V_{GS} = 0, f = 200 \text{ MHz})$	Yfs	_	5.6	_	mmhos
Reverse Transfer Admittance	$(V_{DS} = 15 \text{ Vdc}, V_{GS} = 0, f = 200 \text{ MHz})$	Y _{rs}	_	1.0	_	mmhos
Input Capacitance	$(V_{DS} = 20 \text{ Vdc}, -V_{GS} = 1.0 \text{ Vdc})$	C _{iss}	_	3.0	_	pF
Reverse Transfer Capacitance	$(V_{DS} = 20 \text{ Vdc}, -V_{GS} = 1.0 \text{ Vdc}, f = 1.0 \text{ MHz})$	C _{rss}	_	0.7	_	pF
Output Capacitance	$(V_{DS} = 20 \text{ Vdc}, -V_{GS} = 1.0 \text{ Vdc}, f = 1.0 \text{ MHz})$	Coss	_	0.9	_	pF
Cut-off Frequency(3)	$(V_{DS} = 15 \text{ Vdc}, V_{GS} = 0)$	F _(Yfs)	_	700	_	MHz

^{3.} The frequency at which g_{fS} is 0.7 of its value at 1 kHz.

COMMON SOURCE CHARACTERISTICS ADMITTANCE PARAMETERS

 $(V_{DS} = 15 \text{ Vdc}, T_{channel} = 25^{\circ}C)$

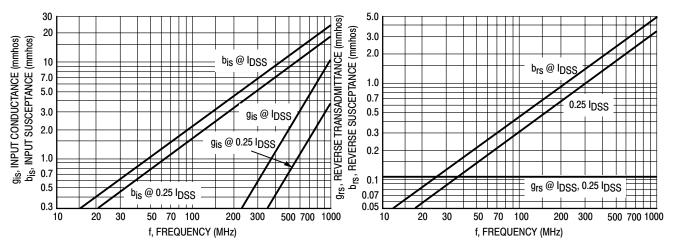


Figure 1. Input Admittance (yis)

Figure 2. Reverse Transfer Admittance (yrs)

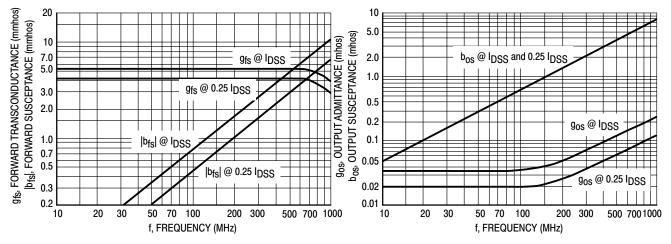
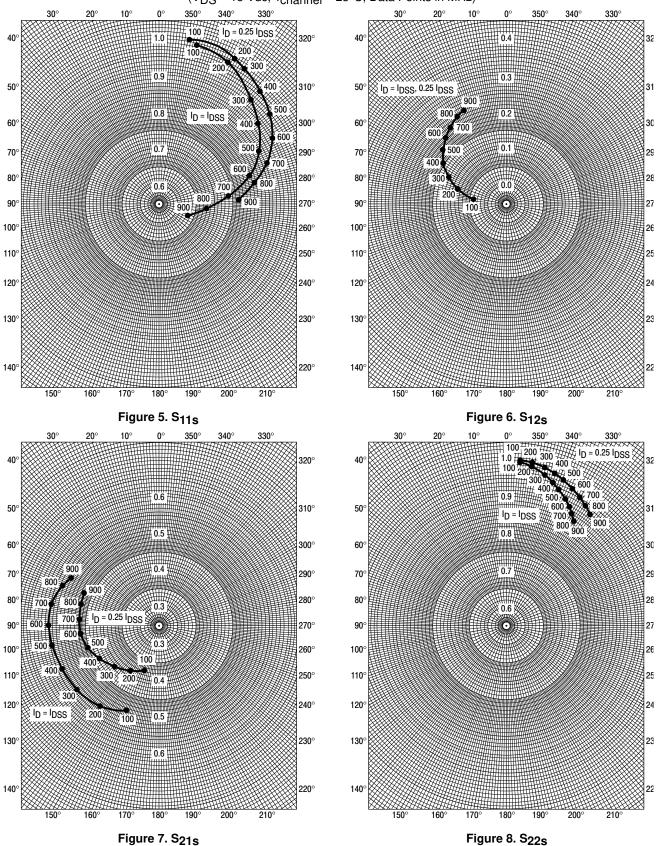


Figure 3. Forward Transadmittance (yfs)

Figure 4. Output Admittance (yos)

COMMON SOURCE CHARACTERISTICS S-PARAMETERS

 $(V_{DS} = 15 \text{ Vdc}, T_{channel} = 25^{\circ}C, Data Points in MHz)$



COMMON GATE CHARACTERISTICS ADMITTANCE PARAMETERS

(V_{DG} = 15 Vdc, T_{channel} = 25°C)

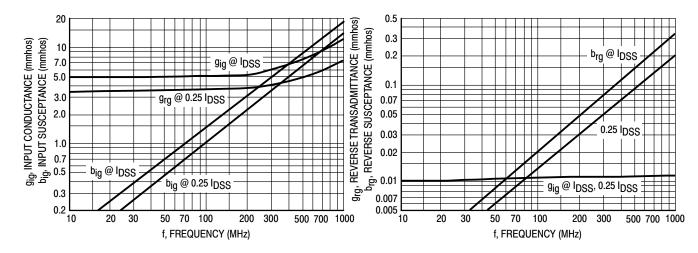


Figure 9. Input Admittance (yig)

Figure 10. Reverse Transfer Admittance (yrg)

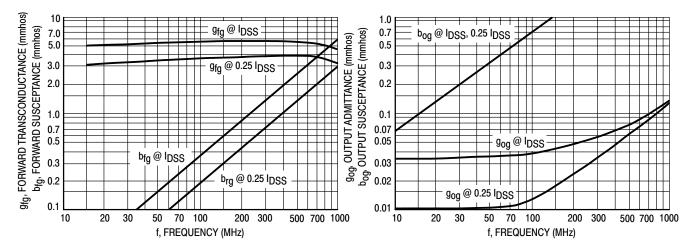
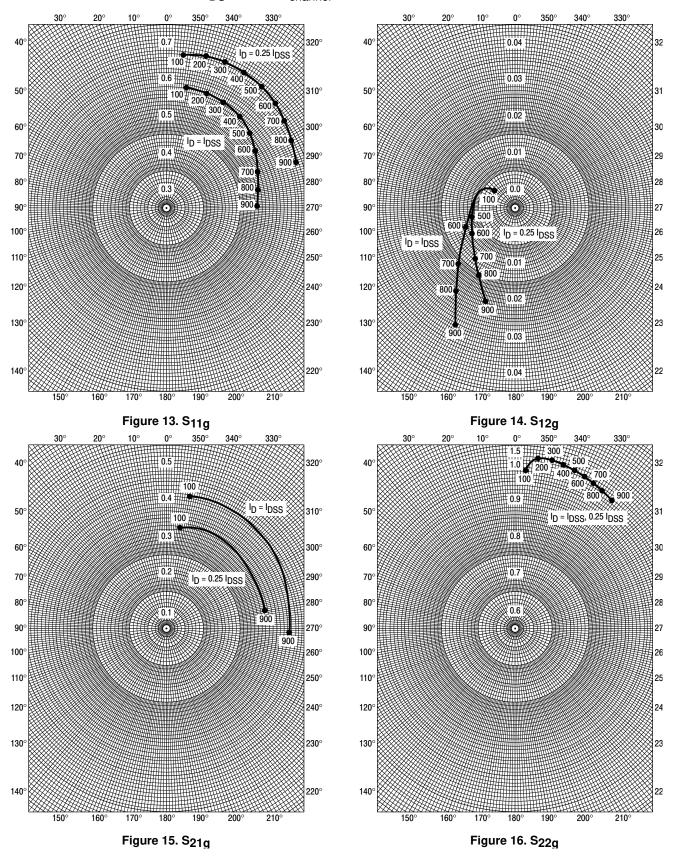


Figure 11. Forward Transfer Admittance (yfg)

Figure 12. Output Admittance (yog)

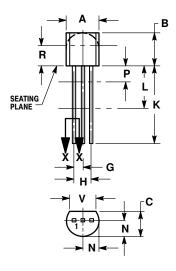
COMMON GATE CHARACTERISTICS S-PARAMETERS

 $(V_{DS} = 15 \text{ Vdc}, T_{channel} = 25^{\circ}C, Data Points in MHz)$



PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 ISSUE AL





STYLE 22:
PIN 1. SOURCE
2. GATE
3. DRAIN

STYLE 23:
PIN 1. GATE
2. SOURCE
3. DRAIN

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.20	
В	0.170	0.210	4.32	5.33	
C	0.125	0.165	3.18	4.19	
D	0.016	0.021	0.407	0.533	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.015	0.020	0.39	0.50	
K	0.500	-	12.70		
L	0.250		6.35		
N	0.080	0.105	2.04	2.66	
P		0.100		2.54	
R	0.115		2.93		
٧	0.135		3.43		

Notes

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